Rev.E Mar.-2016

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SOT-89 PNP Silicon PNP transistor in a SOT-89 Plastic Package.

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hFE VCE(sat)

High DC Current Gain, Low Collector to Emitter Saturation Voltage.

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General purpose amplifier and switching.

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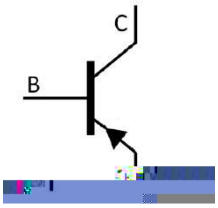

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PIN1 Base PIN 2 Collector PIN 3 Emitter

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h_{FE} Range	100 300
Marking	H2A

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	450	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}					

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

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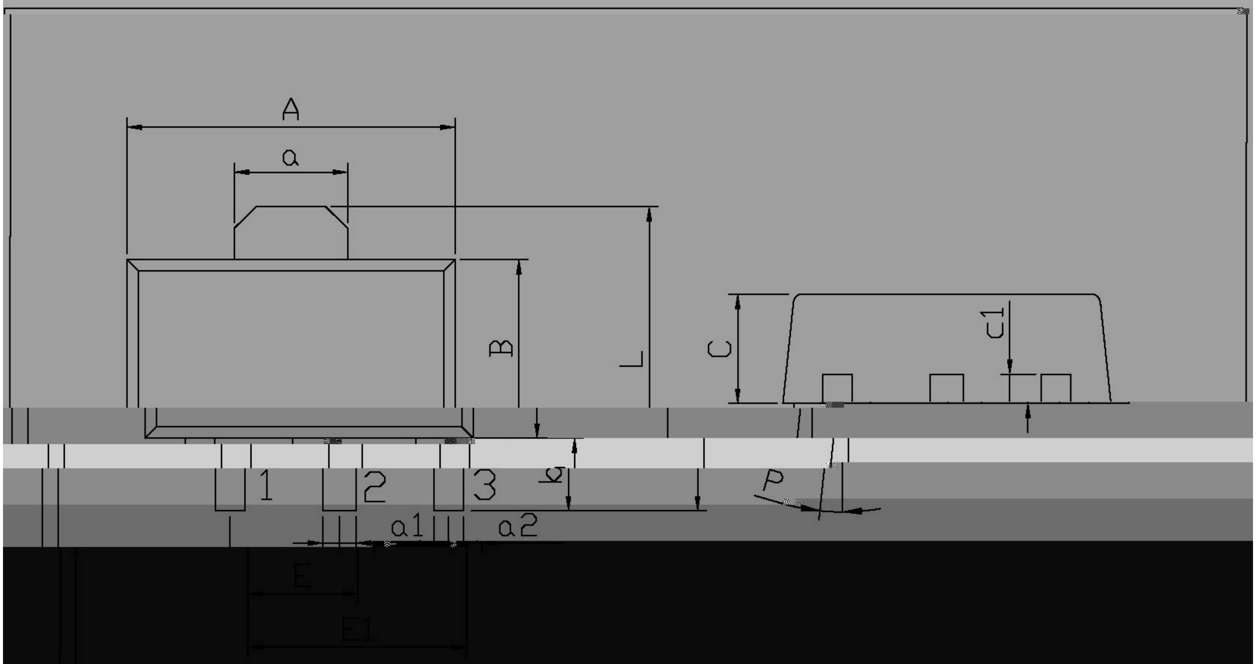
SOT-89 单位：mm



Dimensions in millimeters

	Min	Max		Min	Max
A	4.4	4.7	a1	0.36	0.56
B	2.35	2.65	a2	0.30	0.50
L	3.878	4.478	C	1.40	1.70
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
E1	2.80	3.20			
b	0.80	1.20			

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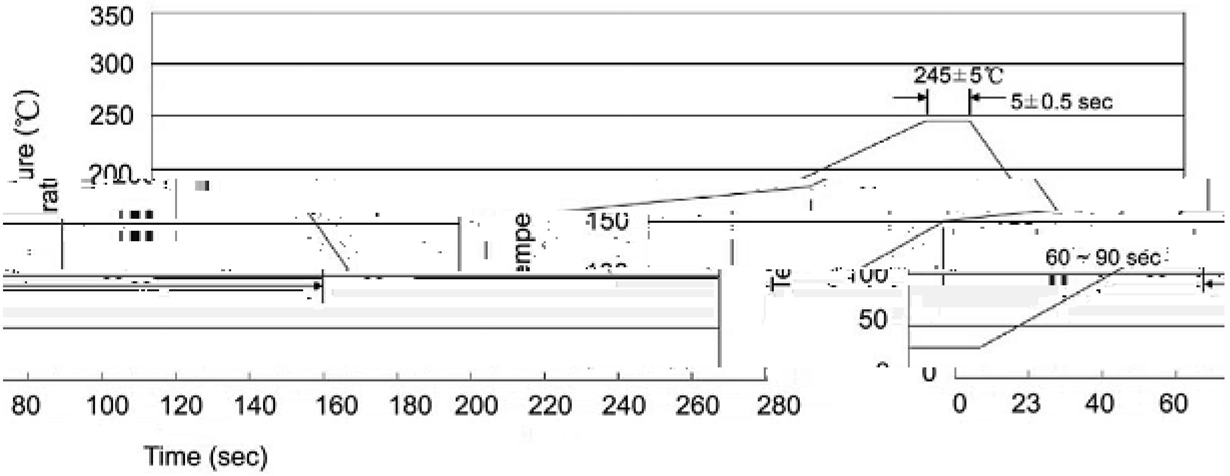

	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.